

μ SR studies on antiferromagnet $\text{RRu}_2\text{Al}_{10}$ ($\text{R} = \text{Sm}, \text{Gd}$)

H. Tanida,^{*1,*3} H. Guo,^{*1,*2} I. Kawasaki,^{*1} M. Sera,^{*3} T. Nishioka,^{*4} M. Matsumura,^{*4}
I. Watanabe,^{*1} and Z. Xu^{*2}

The Kondo semiconductor $\text{CeT}_2\text{Al}_{10}$ ($\text{T} = \text{Ru}, \text{Os}$) with an orthorhombic-type structure shows a unique antiferromagnetic (AFM) order at $T_0 \sim 30$ K.^{1,2)} This compound exhibits numerous unusual electronic properties that can be ascribed to the strong electron correlation between conduction and localized $4f$ electrons, namely, the $c-f$ hybridization effect, by which a renormalized quasi-particle state with heavy effective electron mass is formed in the case of many Ce- or Yb-based intermetallic compounds. However, in the class of materials known as the Kondo semiconductors or insulators, a temperature-dependent energy gap is formed instead. One of the most salient features of this system is magnetic anisotropy in the AFM ordered state. Since the magnetic susceptibility shows a large anisotropy of $\chi_a \gg \chi_c \gg \chi_b$, an AFM ordered moment (m_{AF}) is expected to be parallel to the a -axis in the AFM ordered state. However, $m_{\text{AF}} \parallel c$ is realized, as was revealed by neutron scattering and ^{27}Al NMR/NQR studies.³⁻⁵⁾ The AFM structure is not robust and is easily tuned by magnetic field⁴⁾, pressure⁶⁾, or chemical doping.⁷⁻⁹⁾ This indicates that magnetic exchange interactions are not a key parameter for this magnetic ordering, but there could be an unknown parameter related to the strong $c-f$ hybridization effect, which must be related to the extraordinary high transition temperature of $T_0 \sim 30$ K.

We previously performed μ SR experiments on the above undoped and Rh-doped $\text{CeRu}_2\text{Al}_{10}$. The results have been published elsewhere.⁹⁾ One of the residual problems is the serious inconsistency in the temperature dependence of internal fields (H_{int}) between two muon sites, that is, one component shows a usual mean-field behavior, but the other does not. To address this problem, we planned to perform zero-field μ SR on related antiferromagnets with more localized $4f$ -electron character, $\text{RRu}_2\text{Al}_{10}$ ($\text{R} = \text{Nd}, \text{Sm}, \text{and Gd}$). These compounds are worthy of investigation for their AFM ordered state; for instance, in the sample $\text{R} = \text{Gd}$, m_{AF} is suggested to be parallel to the $[011]$ direction, although a simple dipole-field calculation suggests that m_{AF} prefers the a -axis direction.¹⁰⁾ In ref. 9, a possible origin of this discrepancy was suggested to be the zig-zag chain structure of Gd sites along the c -axis direction.

Figure 1 shows the zero-field time spectra of

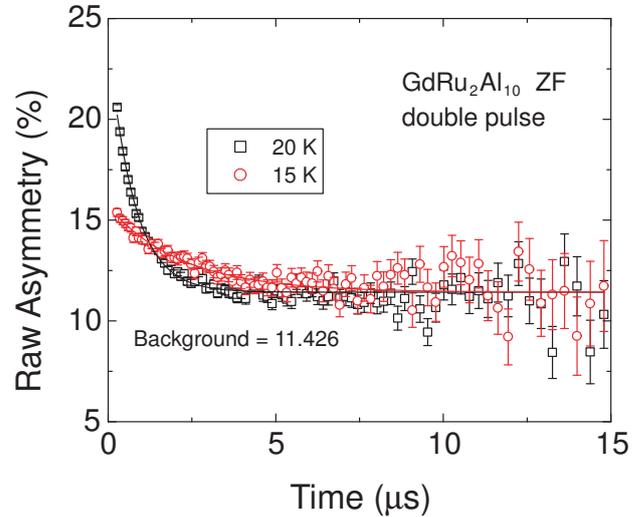


Fig. 1. Zero-field time spectra of $\text{GdRu}_2\text{Al}_{10}$ at $T = 20$ and 15 K under double-pulse-beam condition.

$\text{GdRu}_2\text{Al}_{10}$ at $T = 20$ K and 15 K; the data were recorded under double-pulse-beam condition. We found that the initial asymmetry is reduced when the temperature is lowered below the AFM transition temperature of $T_N = 17$ K. This is clear evidence for magnetic ordering. Since H_{int} is expected to be large because of the large magnetic moment of Gd- $4f$ electrons, we should use single-pulse condition with much greater time resolution than that of the double-pulse condition. However, we had to use the double-pulse condition within our beam time because we could not break the extrinsic noise resulting from the kicker operation. Within the present resolution, we could not identify any muon-spin precession behavior, and thus, from the zero field measurement, we could not obtain quantitative information on H_{int} .

References

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^{*1} RIKEN Nishina Center

^{*2} Department of Physics and State Key Laboratory of Silicon Materials, Zhejiang University

^{*3} AdSM, Hiroshima University

^{*4} Graduate school of Integrated Arts and Science, Kochi University